

Silicon Bridge Rectifier

CBR1-D100S

1000V / 1A

DATASHEET

OEM – Central Semiconductor Corp.

Source: Central Databook 2004

CBR1-D020S SERIES
SURFACE MOUNT
1 AMP DUAL IN LINE
SILICON BRIDGE RECTIFIER



CentralTM

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBR1-D020S series types are silicon full wave bridge rectifiers mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips.

NOTE: Also available in Fast Recovery, please contact factory for details.

MARKING CODE: FULL PART NUMBER

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL	CBR1-D020S	CBR1-D040S	CBR1-D060S	CBR1-D080S	CBR1-D100S	UNITS
Peak Repetitive Reverse Voltage	V _{RRM}	200	400	600	800	1000	V
DC Blocking Voltage	V _R	200	400	600	800	1000	V
RMS Reverse Voltage	V _{R(RMS)}	140	280	420	560	700	V
Average Forward Current (T _A =50°C)	I _O			1.0			A
Peak Forward Surge Current	I _{FSM}			50			A
Rating for Fusing (t<8.35ms)	I _{RT}			10			A ² s
Operating and Storage							
Junction Temperature	T _J , T _{stg}			-65 to +150			°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

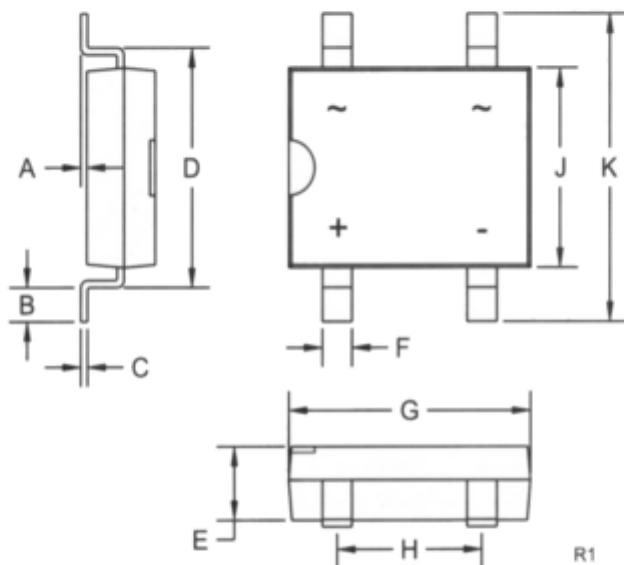
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _R	V _R =Rated V _{RRM}			10	μA
I _R	V _R =Rated V _{RRM} , T _A =125°C			0.5	mA
V _F	I _F =1.0A			1.1	V
C _J	V _R =4.0V, f=1.0MHz		25		pF

For Typical Electrical Characteristic Data for this device, please see Process CPD05 on page 875.



CBR1-D020S SERIES
 SURFACE MOUNT
 1 AMP DUAL IN LINE
 SILICON BRIDGE RECTIFIER

SMDIP CASE - MECHANICAL OUTLINE



MARKING CODE:
 FULL PART NUMBER

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.008	0.10	0.20
B	0.040	0.060	1.02	1.52
C	0.009		0.23	
D	0.290	0.310	7.37	7.87
E	0.086	0.098	2.18	2.49
F	0.038	0.042	0.97	1.07
G	0.316	0.335	8.03	8.51
H	0.195	0.205	4.95	5.21
J	0.245	0.255	6.22	6.48
K	0.360	0.410	9.14	10.41

SMDIP (REV: R1)

DATA SHEETS

R2 (13-November 2002)